FMH07N90E

FUJI POWER MOSFET

Super FAP-E^3 series

N-CHANNEL SILICON POWER MOSFET

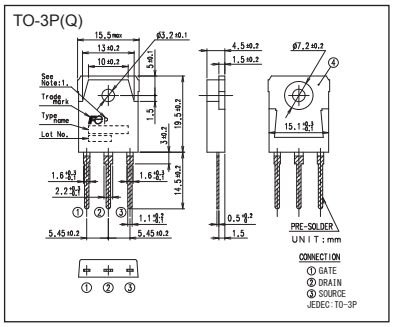
Features

Maintains both low power loss and low noise
Lower R_{DS}(on) characteristic
More controllable switching dv/dt by gate resistance
Smaller V_{GS} ringing waveform during switching
Narrow band of the gate threshold voltage (4.0±0.5V)
High avalanche durability

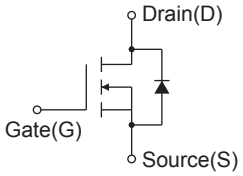
Applications

Switching regulators
UPS (Uninterruptible Power Supply)
DC-DC converters

Outline Drawings [mm]



Equivalent circuit schematic



Maximum Ratings and Characteristics

Absolute Maximum Ratings at Tc=25°C (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V_{DS}	900	V	
	V_{DSX}	900	V	V_{GS} = -30V
Continuous Drain Current	I_D	±7	A	
Pulsed Drain Current	I_{DP}	±28	A	
Gate-Source Voltage	V_{GS}	±30	V	
Repetitive and Non-Repetitive Maximum AvalancheCurrent	I_{AR}	7	A	Note*1
Non-Repetitive Maximum Avalanche Energy	E_{AS}	396.3	mJ	Note*2
Repetitive Maximum Avalanche Energy	E_{AR}	14.5	mJ	Note*3
Peak Diode Recovery dV/dt	dV/dt	2.1	kV/μs	Note*4
Peak Diode Recovery -di/dt	-di/dt	100	A/μs	Note*5
Maximum Power Dissipation	P_D	2.5	W	Ta=25°C
		145		Tc=25°C
Operating and Storage Temperature range	T_{ch}	150	°C	
	T_{stg}	-55 to + 150	°C	

Electrical Characteristics at Tc=25°C (unless otherwise specified)

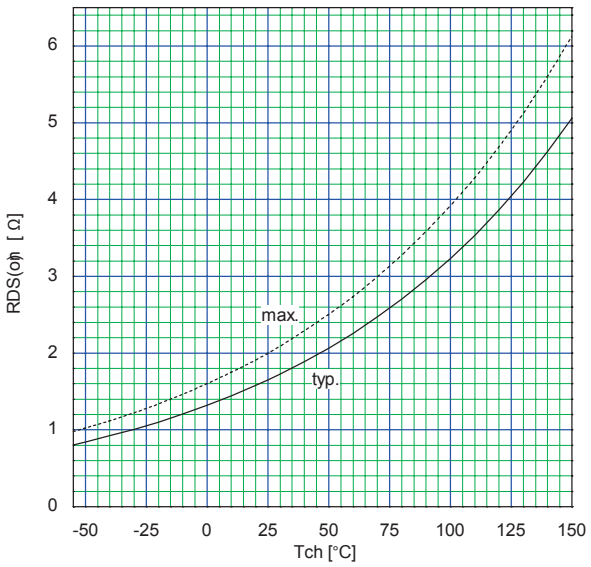
Description	Symbol	Conditions		min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V		900	-	-	V
Gate Threshold Voltage	V_{GS} (th)	I_D=250μA, V_{DS}=V_{GS}		3.5	4.0	4.5	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=900V, V_{GS}=0V	T_{ch}=25°C	-	-	25	μA
		V_{DS}=720V, V_{GS}=0V	T_{ch}=125°C	-	-	250	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V		-	10	100	nA
Drain-Source On-State Resistance	R_{DS} (on)	I_D=3.5A, V_{GS}=10V		-	1.65	2.0	Ω
Forward Transconductance	g_{fs}	I_D=3.5A, V_{DS}=25V		4.2	8.4	-	S
Input Capacitance	Ciss	V_{DS}=25V		-	1200	1800	pF
Output Capacitance	Coss	V_{GS}=0V		-	115	175	
Reverse Transfer Capacitance	Crss	f=1MHz		-	8.5	13	
Turn-On Time	td(on)	V_{cc}=600V		-	33	53	ns
	tr	V_{GS}=10V		-	32	45	
Turn-Off Time	td(off)	I_D=3.5A		-	110	165	
	tf	R_G=36Ω		-	32	45	
Total Gate Charge	Q_G	V_{cc}=450V		-	39	59	nC
Gate-Source Charge	Q_{GS}	I_D=7A		-	10	15	
Drain-Source Crossover Charge	Q_{SW}	V_{GS}=10V		-	3.6	5.5	
Gate-Drain Charge	Q_{GD}			-	15	23	
Avalanche Capability	I_{AV}	L=5.93mH, T_{ch}=25°C		7	-	-	A
Diode Forward On-Voltage	V_{SD}	I_F=7A, V_{GS}=0V, T_{ch}=25°C		-	0.90	1.35	V
Reverse Recovery Time	trr	I_F=7A, V_{GS}=0V		-	1.65	-	μS
Reverse Recovery Charge	Qrr	-di/dt=100A/μs, Tch=25°C		-	11	-	μC

Thermal Characteristics

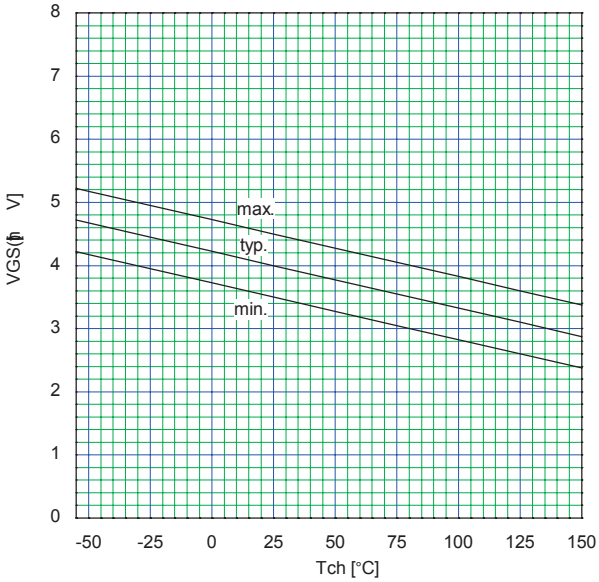
Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	Rth (ch-c)	Channel to case			0.862	°C/W
	Rth (ch-a)	Channel to ambient			50.0	°C/W

Note *1 : Tch≤150°C
Note *2 : Stating Tch=25°C, I_{AS}=2.8A, L=92.7mH, Vcc=90V, R_G=10Ω
E_{AS} limited by maximum channel temperature and avalanche current.
See to 'Avalanche current' graph.
Note *3 : Repetitive rating : Pulse width limited by maximum channel temperature.
See to the 'Transient Themal impeadance' graph.
Note *4 : I_F≤-I_D, -di/dt=100A/μs, Vcc≤BV_{DSS}, Tch≤150°C.
Note *5 : I_F≤-I_D, dv/dt=2.1kV/μs, Vcc≤BV_{DSS}, Tch≤150°C.

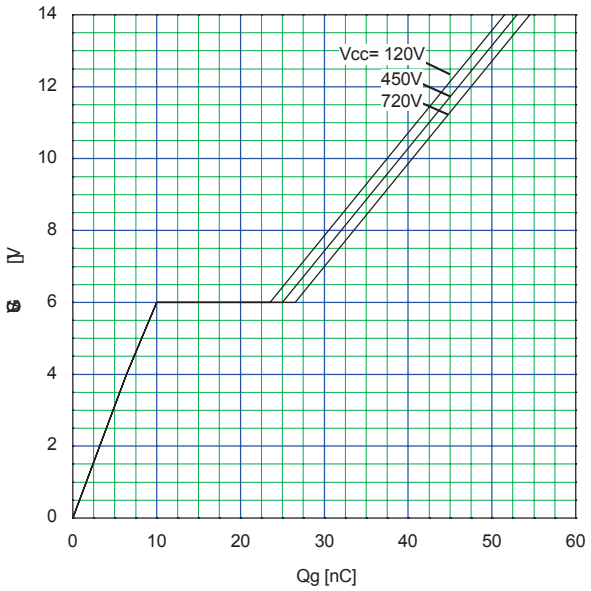
Drain-Source On-state Resistance
RDS(on)=f(Tch):ID=3.5A, VGS=10V



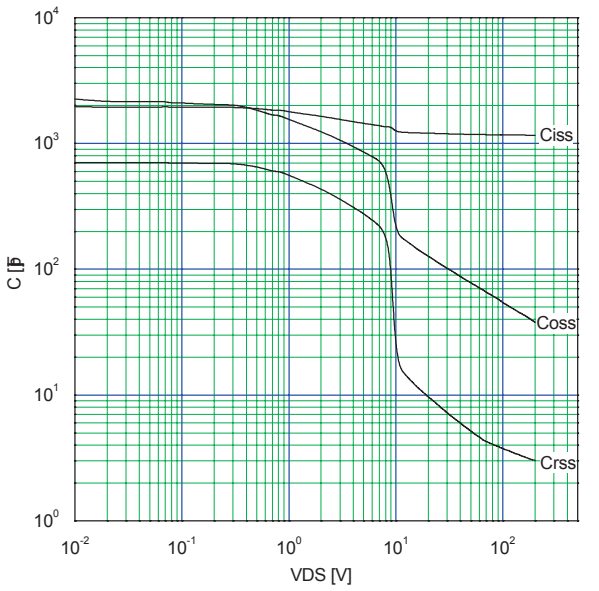
Gate Threshold Voltage vs. Tch
VGS(th)=f(Tch):VDS=VGS, ID=250μA



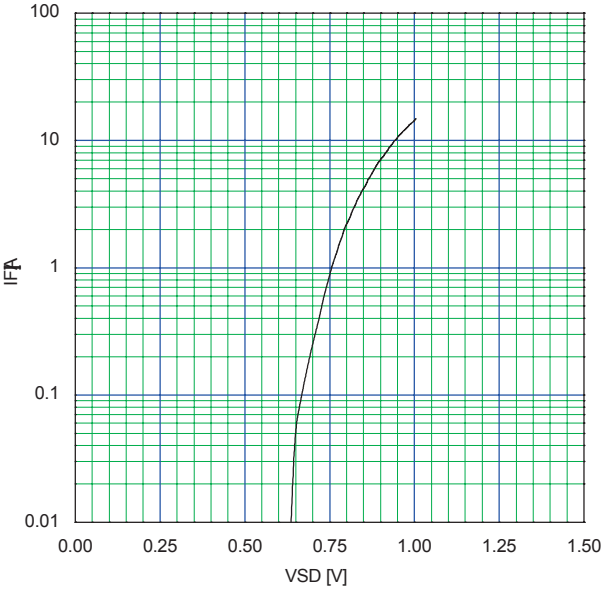
Typical Gate Charge Characteristics
VGS=f(Qg):ID=7A, Tch=25°C



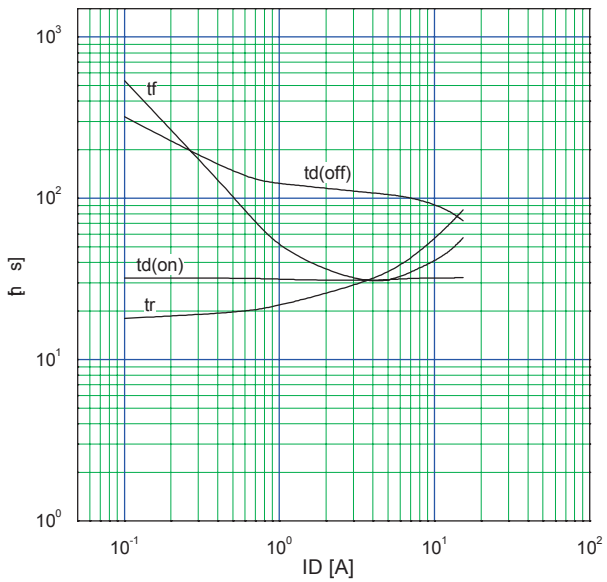
Typical Capacitance
C=f(VDS):VGS=0V, f=1MHz



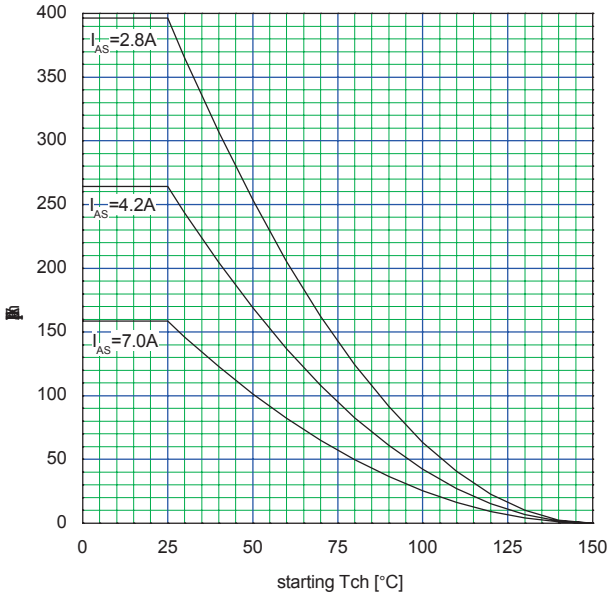
Typical Forward Characteristics of Reverse Diode
IF=f(VSD):80 μs pulse test, Tch=25 °C



Typical Switching Characteristics vs. ID
t=f(ID):Vcc=600V, VGS=10V, RG=3Ω



Maximum Avalanche Energy vs. starting Tch
E(AV)=f(starting Tch):Vcc=90V, I(AV)<=7A



Maximum Transient Thermal Impedance
Zth(ch-c)=f(t):D=0